

Vishay Siliconix

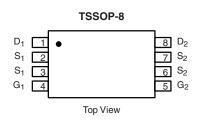
# Dual N-Channel 2.5-V (G-S) MOSFET

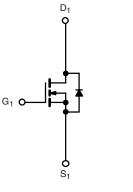
PRODUCT SUMMARY				
V <sub>DS</sub> (V)	<b>R<sub>DS(on)</sub> (Ω)</b>	I <sub>D</sub> (A)		
20	0.045 at V <sub>GS</sub> = 4.5 V	3.9		
	0.055 at V <sub>GS</sub> = 3.0 V	3.5		
	0.065 at V <sub>GS</sub> = 2.5 V	3.0		

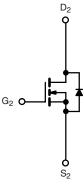
### FEATURES

• Halogen-free









Ordering Information: Si6925ADQ-T1-GE3 (Lead (Pb)-free and Halogen-free)

N-Channel MOSFET

N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T <sub>A</sub> = 25 °C, unless otherwise noted						
Parameter		Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V <sub>DS</sub>	20		v	
Gate-Source Voltage		V <sub>GS</sub>	± 12			
Continuous Drain Qurrent (T 150 °C)	T <sub>A</sub> = 25 °C	- I <sub>D</sub>	3.9	3.3	- 	
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 70 °C		3.1	2.6		
Pulsed Drain Current (10 µs Pulse Width)		I <sub>DM</sub>	30		A	
Continuous Source Current (Diode Conduction) <sup>a</sup>		۱ <sub>S</sub>	1.0	0.72		
	T <sub>A</sub> = 25 °C	- P <sub>D</sub>	1.13	0.80	W	
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 70 °C		0.72	0.51	vv	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
	t ≤ 10 s	- R <sub>thJA</sub> R <sub>thJF</sub>	186	110		
Maximum Junction-to-Ambient <sup>a</sup>	Steady State		125	155	°C/W	
Maximum Junction-to-Foot (Drain)	Steady State		65	85		

Notes:

a. Surface Mounted on FR4 board,  $t \leq$  10 s.

For SPICE model information via the Worldwide Web: http://www.vishay.com/www/product/spice.htm.

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<b>SPECIFICATIONS</b> $T_J = 25 \circ 0$ Parameter	Symbol	Test Conditions	Min.	Typ. <sup>a</sup>	Max.	Unit	
Static	<u> </u>				<u> </u>		
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = 250 \ \mu A$	0.6		1.8	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 12 V$			± 100	nA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}$			1		
		$V_{DS} = 20 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 70 ^{\circ}\text{C}$			15	μA	
On-State Drain Current <sup>b</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 \text{ V}, \text{ V}_{GS} = 4.5 \text{ V}$	10			А	
Drain-Source On-State Resistance <sup>b</sup>		$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 3.9 \text{ A}$		0.035	0.045		
	R <sub>DS(on)</sub>	$V_{GS} = 3.0 \text{ V}, \text{ I}_{D} = 3.5 \text{ A}$ 0.042			0.055	Ω	
		$V_{GS} = 2.5 \text{ V}, \text{ I}_{D} = 3.0 \text{ A}$		0.050	0.065		
Forward Transconductance <sup>b</sup>	9 <sub>fs</sub>	$V_{DS} = 10 \text{ V}, I_{D} = 3.9 \text{ A}$		14		S	
Diode Forward Voltage <sup>b</sup>	V <sub>SD</sub>	I <sub>S</sub> = 1.0 A, V <sub>GS</sub> = 0 V		0.75	1.1	V	
Dynamic <sup>a</sup>			•	•			
Total Gate Charge	Qg			4.0	6		
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = 6 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 3.9 \text{ A}$		0.9		nC	
Gate-Drain Charge	Q <sub>gd</sub>			1.0			
Gate Resistance	R <sub>g</sub>			1.9		Ω	
Turn-On Delay Time	t <sub>d(on)</sub>			40	60		
Rise Time	t <sub>r</sub>	$V_{DD}$ = 6 V, $R_L$ = 6 $\Omega$		50	75	ns	
Turn-Off Delay Time	t <sub>d(off)</sub>	$\rm I_D \cong 1$ A, $\rm V_{GEN}$ = 4.5 V, $\rm R_g$ = 6 $\Omega$		20	30		
Fall Time	t <sub>f</sub>			10	20		
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 1.0 A, dl/dt = 100 A/μs		20	40		

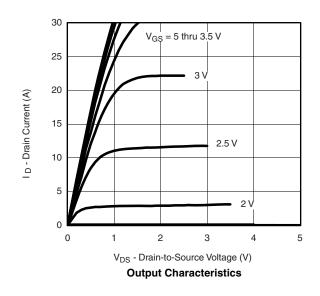
Notes:

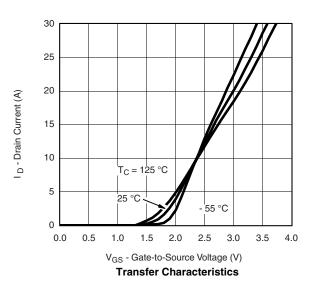
a. Guaranteed by design, not subject to production testing.

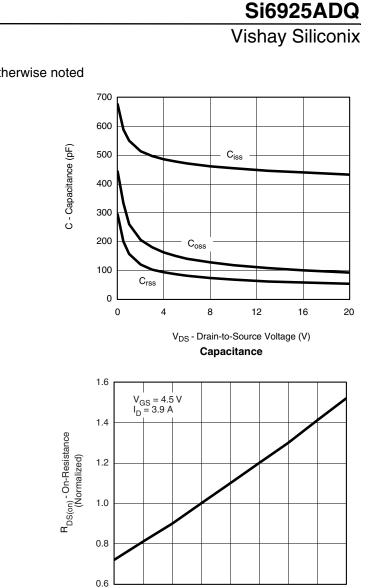
b. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted







T<sub>J</sub> - Junction Temperature (°C) On-Resistance vs. Junction Temperature

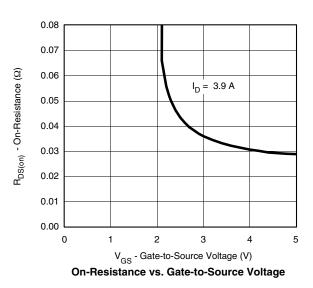
50

75

100

125

150



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

V<sub>GS</sub> = 3.0 V

15

I<sub>D</sub> - Drain Current (A)

**On-Resistance vs. Drain Current** 

2

1

3

Q<sub>q</sub> - Total Gate Charge (nC)

**Gate Charge** 

T<sub>J</sub> = 150 °C

0.6

V<sub>SD</sub> - Source-to-Drain Voltage (V) Source-Drain Diode Forward Voltage

0.8

20

V<sub>GS</sub> = 4.5 V

25

30

5

4

T<sub>J</sub> = 25 °C

1.0

1.2

- 50

- 25

0

25

**VISHAY** 

0.10

0.08

0.06

0.04

0.02

0.00

0

6

5

4

3

2

1

0 🗹

30

10

S - Source Current (A)

 $V_{GS} = 2.5 V$ 

5

 $V_{DS} = 6 V$  $I_{D} = 3.9 A$ 

10

 $R_{DS(on)}$  - On-Resistance ( $\Omega)$ 

V<sub>GS</sub> - Gate-to-Source Voltage (V)

Document Number: 72623 S-81056-Rev. B, 12-May-08

1

0.0

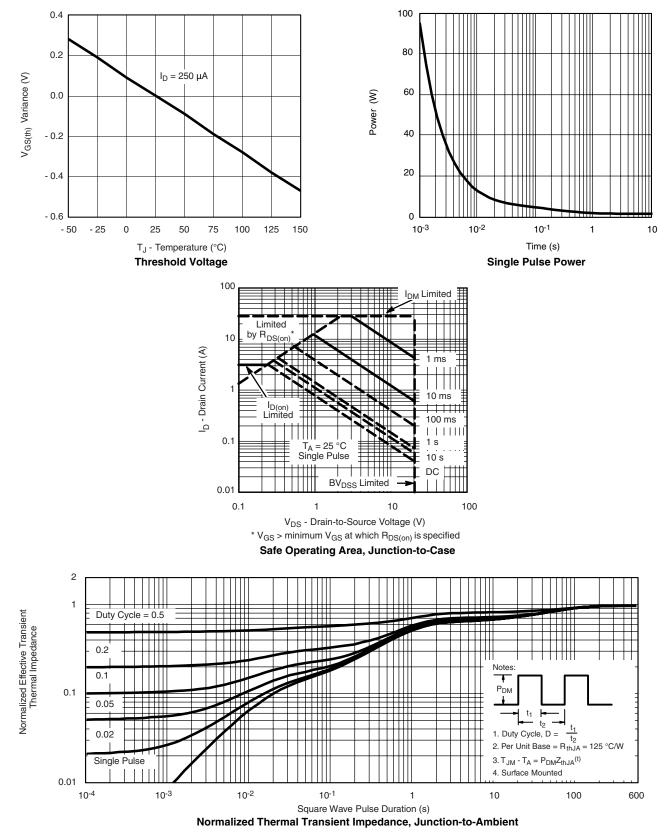
0.2

0.4

## Si6925ADQ

## Vishay Siliconix

### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



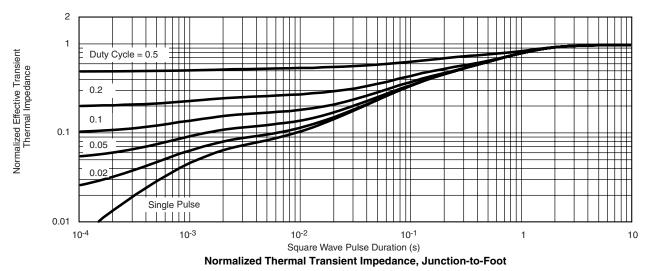
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Si6925ADQ

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#### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see http://www.vishay.com/ppg?72623.



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